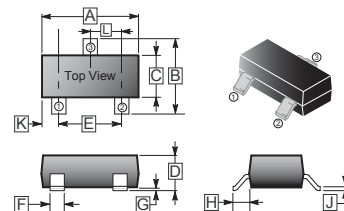


RoHS Compliant Product  
A suffix of "-C" specifies halogen & lead-free

**SOT-23**

**FEATURES**

- High conductance Low Leakage Diode



**MARKING**

Part Name	MMBD1501A	MMBD1503A	MMBD1504A	MMBD1505A
Marking	A11	A13	A14	A15
Circuit				

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.04	G	-	0.18
B	2.10	2.80	H	0.40	0.60
C	1.20	1.60	J	0.08	0.20
D	0.89	1.40	K	0.6	REF.
E	1.78	2.04	L	0.85	1.15
F	0.30	0.50			

**ABSOLUTE MAXIMUM RATINGS (@ Ta = 25°C)**

PARAMETER	SYMBOL	LIMITS	UNIT	
Working Inverse Voltage	$V_R$	200	V	
DC Forward Current	$I_F$	600	mA	
Average Rectifying Current	$I_O$	200	mA	
Total Device Dissipation	$P_D$	350	mW	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W	
Surge Current	$I_{SURGE}$	1 s	1	A
		1 microsecond	2	A
Junction, Storage Temperature	$T_J, T_{STG}$	150, -55~150	°C	

**ELECTRICAL CHARACTERISTICS (at Tamb = 25°C unless otherwise specified)**

Parameters	Symbol	Min.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	$V_{(BR)}$	200	-	V	$I_R = 5\mu A$
Reverse voltage leakage current	$I_R$	-	10	nA	$V_R = 180V$
Forward Voltage	$V_{F1}$	-	0.75	V	$I_F = 1 mA$
	$V_{F2}$	-	0.85	V	$I_F = 10 mA$
	$V_{F3}$	-	0.95	V	$I_F = 50 mA$
	$V_{F4}$	-	1.1	V	$I_F = 100 mA$
	$V_{F5}$	-	1.3	V	$I_F = 200 mA$
	$V_{F6}$	-	1.5	V	$I_F = 300 mA$
Diode Capacitance	$C_D$	-	4	pF	$V_R = 0, f = 1 MHz$

**RATINGS AND CHARACTERISTIC CURVES**

